Si4925DY

Vishay Siliconix



SPECIFICATIONS (T _J = 25° C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ ^a	Max	Unit
Static						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},\ I_{D}=-250\ \mu A$	-1		-3	V
Gate-Body Leakage	I _{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = -30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			-1	- μΑ
		V_{DS} = –30 V, V_{GS} = 0 V, T_J = 55 $^\circ C$			-25	
On-State Drain Current ^b	I _{D(on)}	$V_{DS}\leq-5$ V, V_{GS} = -10 V	-20			A
Drain-Source On-State Resistance ^b	r _{DS(on)}	V_{GS} = -10 V, I _D = -6.3 A		0.024	0.032	Ω
		V_{GS} = -4.5 V, I _D = -5.3 A		0.036	0.045	
Forward Transconductanceb		$V_{DS} = -15 \text{ V}, \text{ I}_{D} = -6.3 \text{ A}$		14		S
Diode Forward Voltage ^b	V _{SD}	$I_{\rm S}$ = -1.7 A, $V_{\rm GS}$ = 0 V		-0.8	-1.2	V
Dynamic ^a						
Total Gate Charge	Qg	V_{DS} = -15 V, V_{GS} = -10 V, I_{D} = -6.3 A		27	50	nC
Gate-Source Charge	Q _{gs}			6		
Gate-Drain Charge	Q _{gd}			4.5		
Turn-On Delay Time	t _{d(on)}	V_{DD} = -15 V, R _L = 15 Ω I _D \cong -1 A, V _{GEN} = -10 V, R _g = 6 Ω		16	20	ns
Rise Time	t _r			10	20	
Turn-Off Delay Time	t _{d(off)}			55	80	
Fall Time	t _f			20	40	
Source-Drain Reverse Recovery Time	t _{rr}	$I_F = -1.7 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$		40	90	1

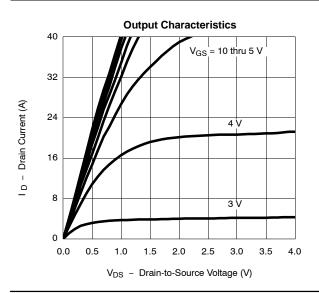
Notes

a.

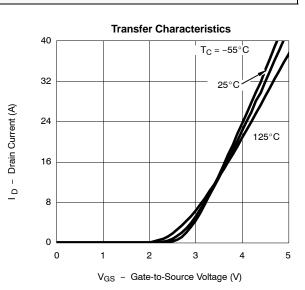
For design aid only; not subject to production testing. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2%. b.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



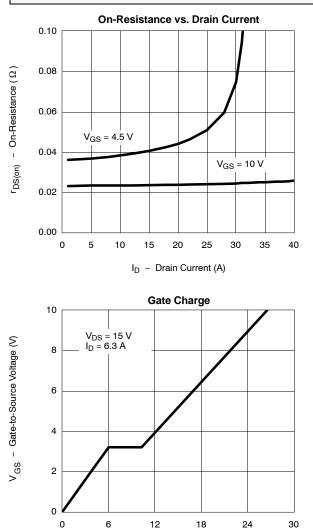
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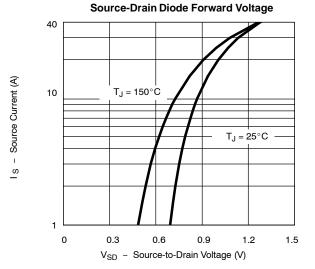


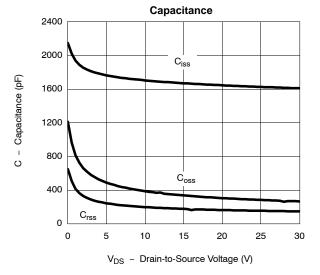
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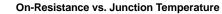
TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

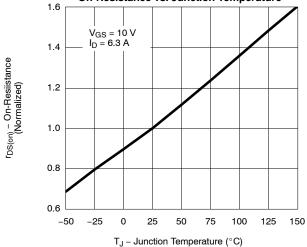


Q_g – Total Gate Charge (nC)

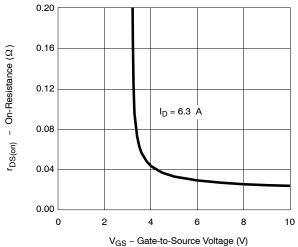








On-Resistance vs. Gate-to-Source Voltage



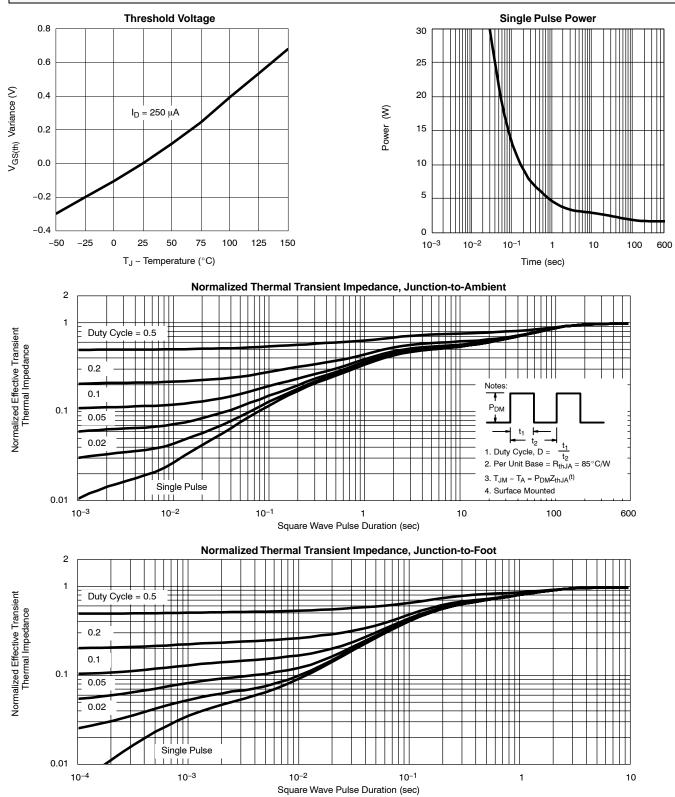
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